

### Description

This 40V,120A N-Channel MOSFET in a TO-263 Plastic Package.

### Features

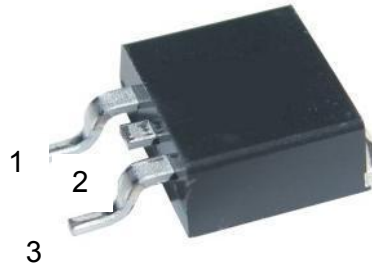
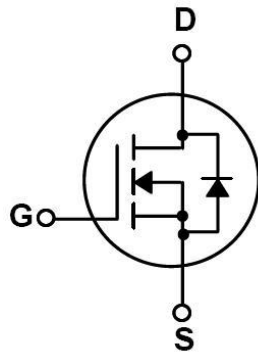
- Ultra Low On-Resistance
- Fast switching
- Halogen-free Product.

### Applications

- These devices are well suited for high efficient
- Switched mode power supplies
- Active power factor correction
- Electronic lamp ballast based on half bridge topology.

$V_{DSS}$	$R_{DS(on)}$ (Typ)	$I_D$
40V	1.6m $\Omega$	120A

### Equivalent Circuit & Pinning



Pin1:Gate

Pin2:Drain

Pin3:Source

**Absolute Maximum Ratings(Ta=25°C)**

Parameter	Symbol	Rating	Unit	
Drain-Source Voltage	$V_{DSS}$	40	V	
Drain Current	$I_D(T_C=25^\circ\text{C})$	120	A	
Pulsed Drain Current	$I_{DM}$	480	A	
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V	
Single Pulsed Avalanche Energy L=0.5mH	$E_{AS}$	482	mJ	
Avalanche Current	$I_{AS}$	35	A	
Total Power Dissipation	$P_D(T_C=25^\circ\text{C})$	187	W	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 175	°C	
Thermal Resistance-Junction to Ambient	t ≤ 10s	$R_{\theta JA}$	15	°C/W
	Steady-State		60	
Thermal Resistance-Junction to Case	Steady-State	$R_{\theta JC}$	0.7	

**Electrical Characteristics(Ta=25°C)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V$ $I_D=250\mu A$	40	44		V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=40V$ $V_{GS}=0V$			1	$\mu A$
Gate-Body Leakage Current Forward	$I_{GSS}$	$V_{GS}=\pm 20V$ $V_{DS}=0V$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1	1.6	3	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=20A$		1.6	2	mΩ
		$V_{GS}=4.5V$ $I_D=10A$		2.1	4	
Forward On Voltage	$V_{SD}$	$V_{GS}=0V$ $I_S=1A$			1.2	V
Input Capacitance	$C_{iss}$	$V_{DS}=25V$ $V_{GS}=0V$ $f=1MHz$		110		pF
Output Capacitance	$C_{oss}$			840		
Reverse Transfer Capacitance	$C_{rss}$			650		

**Electrical Characteristics(Ta=25°C)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Gate resistance	$R_g$	$f=1\text{MHz}$		1.45		$\Omega$
Total Gate Charge	$Q_g(10\text{V})$	$V_{GS}=10\text{V}$ $V_{DS}=20\text{V}$ $I_D=20\text{A}$		68		nC
Total Gate Charge	$Q_g(4.5\text{V})$			28		
Gate Source Charge	$Q_{gs}$			16.5		
Gate Drain Charge	$Q_{gd}$			4.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10\text{V}$ $V_{DS}=20\text{V}$ $R_L=1\Omega$ $R_{GEN}=3\Omega$		12.5		ns
Turn-On Rise Time	$t_r$			9.5		
Turn-Off Delay Time	$t_{d(off)}$			57.5		
Turn-Off Fall Time	$t_f$			10.5		

Electrical Characteristic Curve

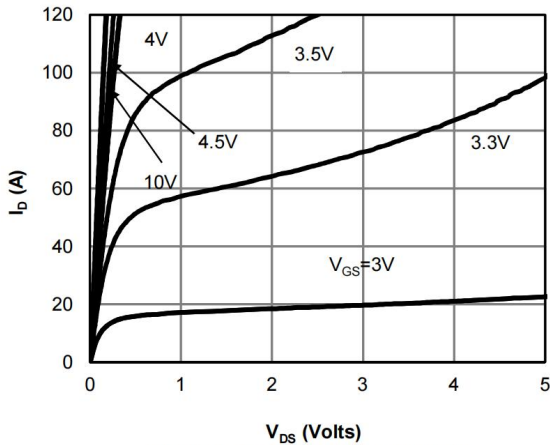


Figure 1: On-Region Characteristics

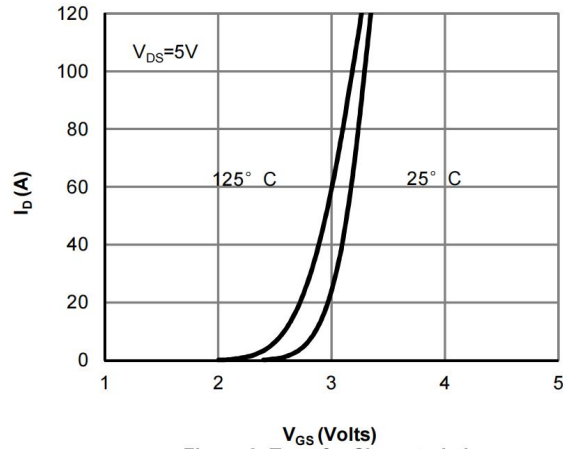


Figure 2: Transfer Characteristics

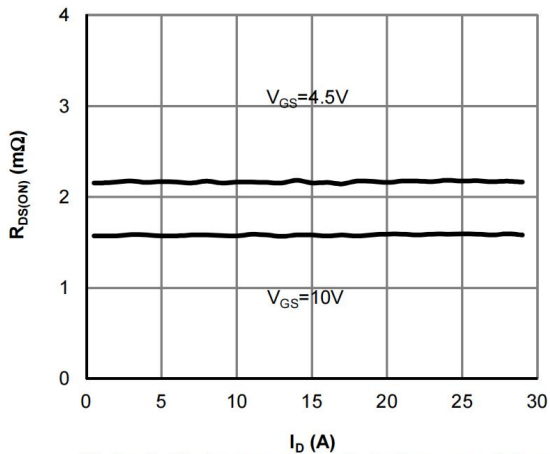


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

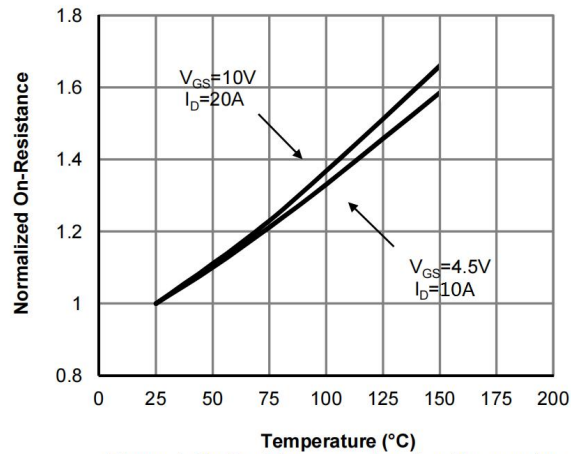


Figure 4: On-Resistance vs. Junction Temperature

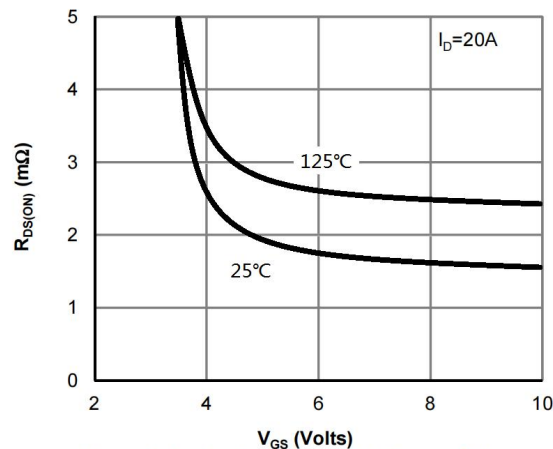


Figure 5: On-Resistance vs. Gate-Source Voltage

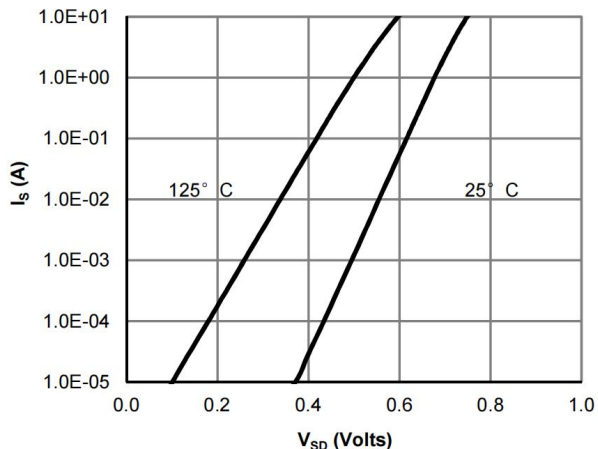
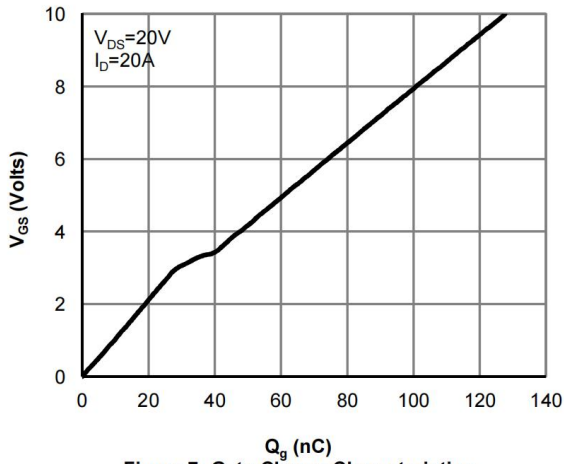
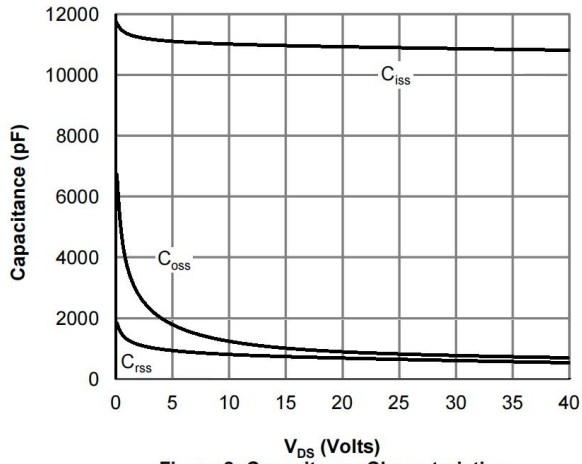


Figure 6: Body-Diode Characteristics

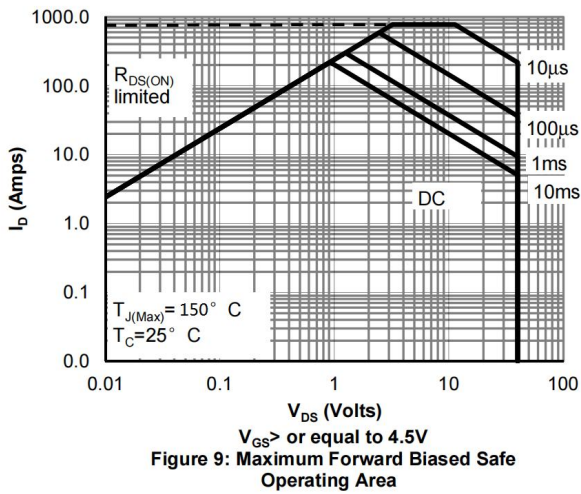
**Electrical Characteristic Curve**



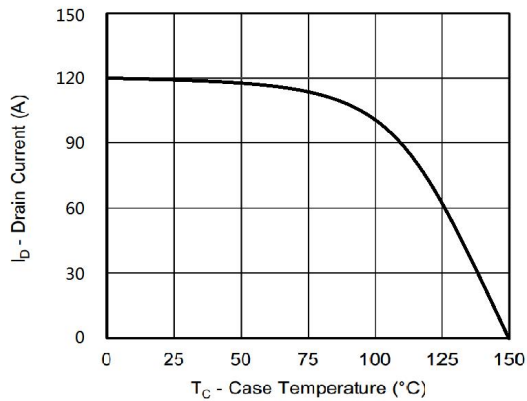
**Figure 7: Gate-Charge Characteristics**



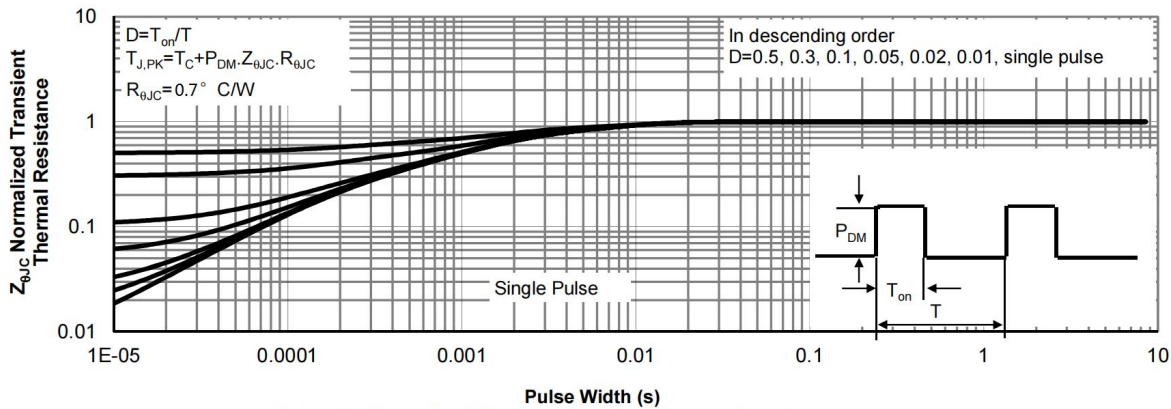
**Figure 8: Capacitance Characteristics**



**Figure 9: Maximum Forward Biased Safe Operating Area**

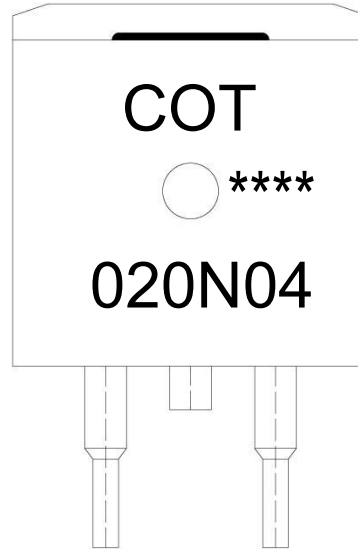


**Figure 10: Maximum Continuous Drain Current vs Case Temperature**



**Figure 11: Normalized Maximum Transient Thermal Impedance**

Marking Instructions



Note:

- COT: Company Code
- 020N04: Product Type.
- \*\*\*\*: Lot No. Code, code change with Lot No.

Packaging SPEC.

REEL INFORMATION

Package Type	Units					Dimension (unit: mm <sup>3</sup> )		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
TO-263	800	1	800	5	4,000	13" x24	360×360×50	385×257×392

TUBE INFORMATION

Package Type	Units					Dimension (unit: mm <sup>3</sup> )		
	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Tube	Inner Box	Outer Box
TO-263	50	20	1,000	5	5,000	532×33×7.0	555×164×50	575×290×180

Package Outline Dimensions

